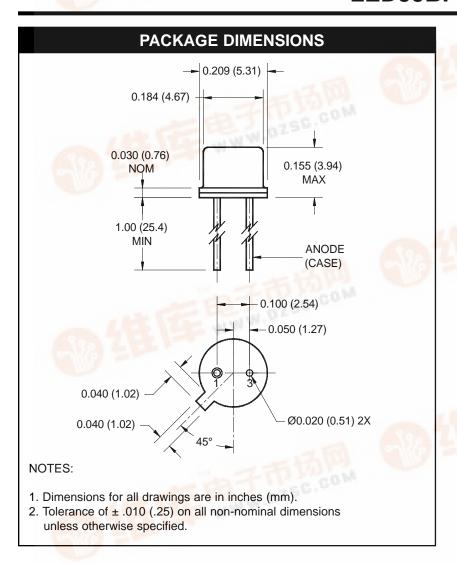
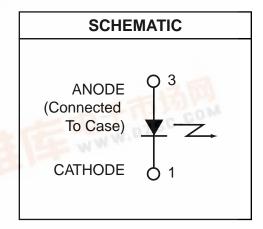


捷多邦,专业PCB打样工厂,24小时加急出货 **GaAs INFRARED EMITTING DIODE**

LED55BF LED55CF LED56F







DESCRIPTION

The LED55BF/LED55CF/LED56F series are 940nm LEDs in a wide angle, TO-46 package.

FEATURES

- Good optical to mechanical alignment
- Mechanically and wavelength matched to the TO-18 series phototransistor
- Hermetically sealed package
- High irradiance level





GaAs INFRARED EMITTING DIODE

LED55BF LED55CF LED56F

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T _{OPR}	-65 to +125	°C					
Storage Temperature	T _{STG}	-65 to +150	°C					
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C					
Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C					
Continuous Forward Current	I _F	100	mA					
Forward Current (pw, 1µs; 200Hz)	I _F	10	A					
Reverse Voltage	V _R	3	V					
Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	170	mW					
Power Dissipation (T _C = 25°C) ⁽²⁾	P _D	1.3	W					

NOTE:

- 1. Derate power dissipation linearly 1.70 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 13.0 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension
- 7. Total power output, P_0 , is the total power radiated by the device into a solid angle of 2 π steradians.

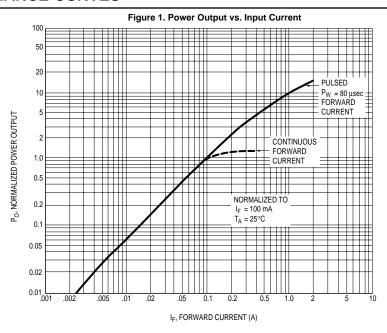
ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)							
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS	
Peak Emission Wavelength	I _F = 100 mA	λ_{PE}	_	940	_	nm	
Emission Angle at 1/2 Power		θ	_	±40	_	Deg.	
Forward Voltage	I _F = 100 mA	V _F	_	_	1.7	V	
Reverse Leakage Current	V _R = 3 V	I _R	_	_	10	μA	
Total Power LED55BF ⁽⁷⁾	I _F = 100 mA	Po	3.5	_	_	mW	
Total Power LED55CF ⁽⁷⁾	I _F = 100 mA	Po	5.4	_	_	mW	
Total Power LED56F ⁽⁷⁾	I _F = 100 mA	Po	1.5	_	_	mW	
Rise Time 0-90% of output		t _r	_	1.0	_	μs	
Fall Time 100-10% of output		t _f	<u> </u>	1.0	_	μs	

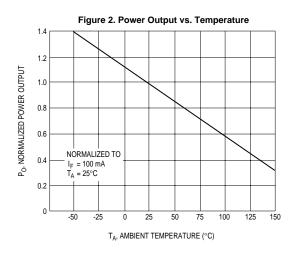


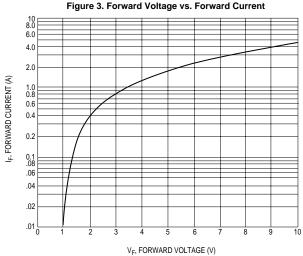
GaAs INFRARED EMITTING DIODE

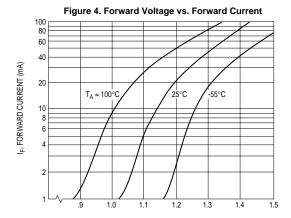
LED55BF LED55CF LED56F

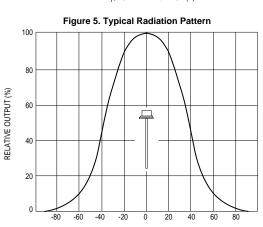
TYPICAL PERFORMANCE CURVES













GaAs INFRARED EMITTING DIODE

LED55BF LED55CF LED56F

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.